

BYT11-600 - BYT11-1000 HIGH EFFICIENCY RECTIFIER DIODES

VOLTAGE RANGE: 600 - 1000V CURRENT: 1.0 A

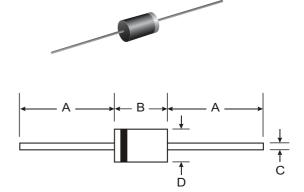
Features

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability

Mechanical Data

- Case: D O 4 1 Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.34 grams (approx.)
- Mounting Position: Any
- Marking: Type Number





DO-41 Plastic				
Dim	Min	Max		
Α	25.40	_		
В	4.06	5.21		
С	0.71	0.864		
D	2.00	2.72		
All Dimensions in mm				

Maximum Ratings and Electrical Characteristics T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	BYT11-600	BYT11-800	BYT11-1000	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vrrm Vrwm Vr	600	800	1000	V
RMS Reverse Voltage	VR(RMS)	420	560	700	V
Average Rectified Output Current (Note 1) $@T_A = 55^{\circ}C$	lo	1.0			A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	FSM	20			A
Forward Voltage $@I_F = 1.0A$	Vfm	1.3			V
Peak Reverse Current $@T_A = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_A = 100^{\circ}C$	IRM	20			μΑ
Reverse Recovery Time (Note 2)	trr	100			nS
Typical Junction Capacitance (Note 3)	Cj	15			pF
Operating Temperature Range	Tj	-65 to +125		°C	
Storage Temperature Range	Tstg	-65 to +150		°C	

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case

2. Measured with IF = 0.5A, IR = 1.0A, IRR = 0.25A. See figure 5.

3. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.